



94

AD A 0 6 7

RESEARCH AND DEVELOPMENT TECHNICAL REPORT CORADCOM- 77-0158-F

MICROSTRIP MILLIMETER WAVE ANTENNA STUDY

Michael A. Weiss Richard B. Cassell Ball Aerospace Systems Division Boulder, Colo. 80306

April 1979 Final Report for Period 1 Aug. 1977 - 31 Oct. 1978

DISTRIBUTION STATEMENT Approved for public release; distribution unlimited.

distribution unlimited.

D D C
PROPINITE

APR 27 1979

EUEUU E

B

Prepared for: CENCOMS

CORADCOM

US ARMY COMMUNICATION RESEARCH & DEVELOPMENT COMMAND FORT MONMOUTH, NEW JERSEY 07703

79 04 25 098

DOC FILE COPY,

### NOTICES

#### Disclaimers

The citation of trade names and names of manufacturers in this report is not to be construed as official Government indorsement or approval of commercial products or services referenced herein.

### Disposition

Destroy this report when it is no longer needed. Do not return it to the originator.

UNCLASSIFIED SECURITY CLASSIFICATION OF THIS PAGE (When Date Entered) **READ INSTRUCTIONS** (/2 REPORT DOCUMENTATION PAGE BEFORE COMPLETING FORM REPORT NUMBER 2. GOVT ACCESSION NO. 3. RECIPIENT'S CATALOG NUMBER CORADCOM 77-0158-F ----TITLE (and Subtitle) Final Report. Microstrip Millimeter Wave Antenna Study. 1 Aug 277 - 31 Oct 78, PERFORMUIG ORG. REPORT NUMBER F78-16 CONTRACT OR GRANT NUMBER(a) 7. AUTHOR(.) Michael A./Weiss DAAB07-77-C-0158 Richard B./ Cassell 10. PROGRAM ELEMENT, PROJECT, TASK AREA & WORK UNIT NUMBERS 9. PERFORMING ORGANIZATION NAME AND ADDRESS Ball Brothers Research Corporation Aerospace Division/ 611102-H48-H2-11-01 Box 1062, Boulder, Colorado 80306 12. REPORT DATE 11. CONTROLLING OFFICE NAME AND ADDRESS April 1979 Cdr, CORADCOM ATTN: DRDCO-COM-RM-4 NUMBER OF PAGES Fort Monmouth, NJ 07703 15. SECURITY CLASS. (of this report) 14. MONITORING AGENCY NAME & ADDRESS(If different fr UNCLASSIFIED 15a. DECLASSIFICATION/DOWNGRADING SCHEDULE 16. DISTRIBUTION STATEMENT (of this Report) Approved for public release; distribution unlimited. 17. DISTRIBUTION STATEMENT (of the abetract entered in Block 20, If different from Report) 18. SUPPLEMENTARY NOTES 19. KEY WORDS (Continue on reverse elde if necessary and identify by block number) Microstrip Array, Millimeter Waves, Receiver Front End, Integrated Microstrip Millimeter Wave Receive Antenna 20. ABSTRACT (Continue on reverse side if necessary and identify by block number) The study was conducted primarily to investigate the feasibility and potential of integrating the front-end mixer circuit of a millimeter wave receiver into a microstrip antenna array. Development was concentrated in three areas: Investigate the practicality of conformal microstrip antennas in the millimeter wavelength region. Specifically a 32 X 32 element array operating at 38.4 GHz was designed, fabricated and tested. (Cont'd)

DD 1 JAN 73 1473 EDITION OF 1 NOV 65 IS OBSOLETE

UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE (When Date Entered)

409767

met

SECURITY CLASSIFICATION OF THIS PAGE(When Data Entered)

20. ABSTRACT (Cont'd)

Investigate possible designs for a front-end mixer circuit (i.e., local oscillator and mixer) which are compatible with the goal of incorporation into the microstrip antenna array. Design, fabricate, and analyze candidate circuits.

Integrate candidate front-end circuit into microstrip antenna array.

NTIS	White Section
DDC	Buff Section
UNANNOUNCE	0 0
JUSTIFICATION	
SAFTE ISSUED IN	AVAU ADUITY DODEN
	AVAILABILITY CODES
	AVAILABILITY CODES

UNCLASSIFIED

SECURITY CLASSIFICATION OF THIS PAGE(When Date Entered)

day was conducted primarily to investigate the reast error in the stoot-end sinker precuse of a militarior out of the stoot of the st



## TABLE OF CONTENTS

Section		Page
	REPORT DOCUMENTATION PAGE	
	TABLE OF CONTENTS	ii
1	THEORY OF MICROSTRIP	
	1.1 Basic Microstrip Antenna Configuration	1
	1.2 Input Impedance and Feed Networks	3
2	38.4 GHz 32x32 ELEMENT ARRAY	
	2.1 Array Design Goals	6
	2.2 Array Design	6
	2.3 Waveguide Feedplate Design	15
	2.4 Test Results	21
	2.5 32x32 Element Array Summary	39
3	RECEIVER FRONT-END CIRCUIT	
	3.1 System Design	42
	3.2 Gunn Effect Oscillator	45
	3.3 Schottky Diode Mixer	48
4	CONCLUSIONS AND RECOMMENDATIONS	
	4.1 Conclusions	53
	4.2 Recommendations	54
	ILLUSTRATIONS	
Figure		
1-1	Linearly Polarized Microstrip Element	1
1-2	Electric Field in Vicinity of Microstrip Element	2
1-3	E-Plane Radiation Pattern of Linearly Polarized Microstrip Element	2
1-4	Typical Microstrip Feed Network	3
1-5	Microstrip Radiator - Cross Section View in E-Plane	4
2-1	2x2 Element Array (≈1.6 x actual size)	7
2-2	E-Plane Radiation Pattern (2x2 element array, 3.07 GHz)	9



# TABLE OF CONTENTS (Cont'd)

Figure		Page
2-3	H-Plane Radiation Pattern (2x2 element array, 3.07 GHz)	10
2-4	4x4 Element Array (6.14 GHz)	11
2-5	E-Plane Radiation Pattern (4x4 element, 6.14 GHz)	12
2-6	H-Plane Radiation Pattern (4x4 element, 6.14 GHz)	13
2-7	4x4 Element Reduced Side-Lobe Array (6.09 GHz)	14
2-8	E-Plane Radiation Pattern (4x4 element reduced side-lobe array, 6.09 GHz)	16
2-9	H-Plane Radiation Pattern (4x4 element reduced side-lobe array, 6.09 GHz)	17
2-10	32x32 Element Reduced Side-Lobe Array,(38.4 GHz)	18
2-11	Waveguide Feedplate Layout	20
2-12	E and H-Plane Radiation Patterns (32x32 element array, 13.8 GHz)	22
2-13	E and H-Plane Radiation Patterns (16x32 element array, 13.8 GHz)	23
2-14	Front View of 32x32 Element Reduced Side-Lobe Array (38.4 GHz)	25
2-15	Back View of 32x32 Element Array (38.4 GHz)	26
2-16	E-Plane Radiation Pattern (Serial #001, 38.0 GHz)	27
2-17	E-Plane Radiation Pattern (Serial #001, 38.4 GHz)	28
2-18	E-Plane Radiation Pattern (Serial #001, 38.7 GHz)	29
2-19	H-Plane Radiation Pattern (Serial #001, 38.0 GHz)	30
2-20	H-Plane Radiation Pattern (Serial #001, 38.4 GHz)	31
2-21	H-Plane Radiation Pattern (Serial #001, 38.7 GHz)	32
2-22	E-Plane Radiation Pattern (Serial #002, 38.1 GHz)	33
2-23	E-Plane Radiation Pattern (Serial #002, 38.4 GHz)	34
2-24	E-Plane Radiation Pattern (Serial #002, 38.7 GHz).	35
2-25	H-Plane Radiation Pattern (Serial #002, 38.1 GHz)	36
2-26	H-Plane Radiation Pattern (Serial #002, 38.4 GHz)	37
2-27	H-Plane Radiation Pattern (Serial #002, 38.7 GHz)	38
3-1	Antenna-Receiver Front-End Block Diagram	42
3-2	Antenna-Receiver System (Front View)	43



# TABLE OF CONTENTS (Cont'd)

Figure		Page
3-3	Antenna-Receiver System (Rear View)	44
3-4	Gunn Oscillator Diagram	45
3-5	Microstrip Oscillator Low Pass Filter Circuit	46
3-6	Microstrip Oscillator Layout Configuration	46
3-7	Computer Printout of Oscillator Output Impedance (Z1)	47
3-8	Oscillator Final Configuration	49
3-9	Layout for Schottky Barrier Diode Mixer	50
3-10	Protection-Bias Network and Mixer Photo	52
Tables		
2-1	Input VSWRs of Model AN152A, Serial Numbers 001 and 002	24
2-2	Loss Budget, S/N 001 (38.4 GHz)	40
2-3	Summary of Array Performance (AN152A)	41



# Section 1 THEORY OF MICROSTRIP

#### 1.1 BASIC MICROSTRIP ANTENNA CONFIGURATION

The linearly polarized microstrip element is basically a two-slot radiator<sup>1</sup> as shown in Figure 1-1. The two slots are separated by a length of very

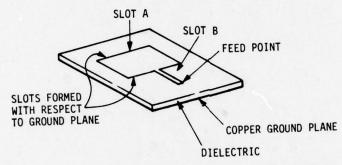


Figure 1-1 Linearly Polarized Microstrip Element

low impedance transmission line. The length of this line can be made just short of a half wavelength so that the complex admittance  $G_S$  of Slot A is transformed to  $G_S^*$  at Slot B where it is added in parallel with the admittance  $G_S$  of Slot B. The result is a real admittance corresponding to the radiation admittance of the antenna plus a small loss component.

Losses depend mostly on the loss tangent of the dielectric material and to a lesser degree on thickness of the dielectric material and the conductivity of the conducting surfaces. The dimensions of the cavity may be expressed analytically as:

Lslot 
$$\approx \frac{\lambda}{2} \left( \frac{1}{\sqrt{\varepsilon_r}} \right)$$
 (1-1)

$$L_{\text{cavity}} \approx \frac{\lambda}{2} \left( \frac{K}{\sqrt{\epsilon_r}} \right), \text{ for } K<1$$
 (1-2)

R. E. Munson, "Conformal Microstrip Antennas and Microstrip Phased Arrays," IEEE Transactions on Antennas and Propagation, Vol. AP-22, No. 1, January 1974, pp. 74-78.



where  $\lambda$  is the free space wavelength, K accounts for radiator edge capacitance, and  $\epsilon_r$  is the real part of the dielectric constant.

Figure 1-2 is a sectional representation of the electric field

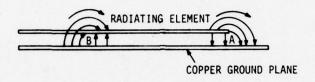


Figure 1-2 Electric Fields in Vicinity of Microstrip Element

in the vicinity of a microstrip radiator. Since the element is about a half wavelength long in the dielectric, the field at one end of the microstrip cavity is reversed from that at the other end of the cavity. However, the radiated fields are in phase and tend to add in the broadside direction. Figure 1-3 shows a typical E-plane pattern attributable to these fields.

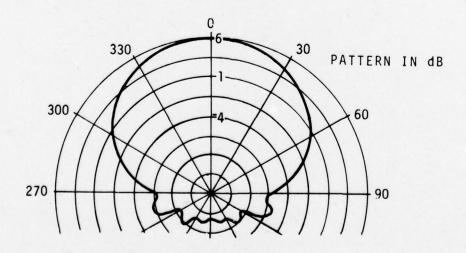


Figure 1-3 E-Plane Radiation Pattern of Linearly Polarized Microstrip Element

#### 1.2 INPUT IMPEDANCE AND FEED NETWORKS

Microstrip antenna elements may be fed by a feed line etched on the same surface as the radiating element or by a feedthrough connection from the rear side of the circuit board.

For etched feed lines the line width required for a given characteristic impedance can be calculated using the well-known formulas for a narrow strip conductor above a conducting ground plane or by reference to an empirically-derived design curve.

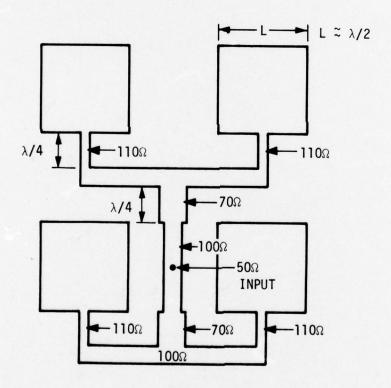


Figure 1-4 Typical Microstrip Feed Network

Figure 1-4 shows a typical feed network using quarterwave transformers to transform the driving impedance of the radiating element to that of the input port.

The microstrip radiator shown in Figure 1-4 is shown in cross-section view in Figure 1-5. Gap A is an infinitesimal slot (in 0.010" microstrip a/ $\lambda \approx 0.03$  at 35 GHz). The admittance of a slot radiator is given in Harrington  $^3$  for

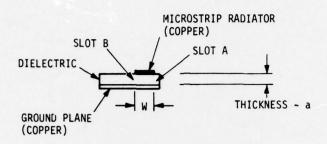


Figure 1-5 Microstrip Radiator - Cross Section View in L-Plane

small  $ka(a/\lambda<0.1)$  which is always the case in microstrip antenna practice.

$$G_a \approx \frac{\pi}{\lambda \eta} \left[ 1 - \frac{(ka)^2}{24} \right]$$
 (1-3)

$$B_a \approx \frac{3.134 - 2 \log ka}{\lambda \eta}$$
 (1-4)

In most microstrip applications ka/24<<1 and the conductance simplifies to  $G_a = \pi/\lambda \eta = 1/(\lambda \cdot 120\Omega)$  or  $R_a' = 120\lambda \Omega$ . The conductance is expressed in per unit length so that the resistance of the Slot A in Figure 1-5 is obtained by dividing  $R_a'$  by the length

$$R_a = \frac{R_a'}{L} = \frac{120\lambda\Omega}{\lambda/2} = 240\Omega$$
 (1-5)

R. F. Harrington, Time Harmonic Electromagnetic Fields, New York, McGraw Hill, p. 276.

In the case of the microstrip radiator, the conductance and susceptance of Slots A and B are equal ( $G_a = G_B$ ,  $B_a = B_B$ ). However, when the admittance of Slot B is transformed across the radiator to the feedpoint of Slot A, it becomes conjugate complex provided the radiator width is chosen appropriately. Since the characteristic impedance of the transmission line formed by radiating element and ground plane is very low, the appropriate width deviates only slightly from  $\frac{\lambda}{2}$ . The admittance at the feedpoint then becomes:

$$Y_F = (G_a + iB_a) + (G_B - iB_B)$$
 (1-6)

and since  $B_a = B_b$  and  $G_a = G_B$ 

$$Y_{F} = 2 G_{a} \tag{1-7}$$

$$R_F = \frac{1}{2G_a} = \frac{R_a}{2} = \frac{240}{2} = 120\Omega$$
 (1-8)

In practice, this is the measured impedance. This theory is accurate in predicting the input impedance for many designs each with different frequencies, thicknesses, and radiator widths.



# Section 2 38.4 GHz 32x32 ELEMENT ARRAY

#### 2.1 ARRAY DESIGN GOALS

The overall goal of this investigation was to establish the practicality of conformal microstrip antennas in the millimeter wavelength region. The investigation utilized results obtained under Contract DAABO7-76-C-0110 as a starting point, and continued with the design, development and fabrication of a 32x32 element antenna array, including feed system, for operation at 38.4 GHz. The input port of the feed system is a standard rectangular waveguide of Type WR-28(RG-96). Antenna array parameters, such as gain, side-lobe level, efficiency, input impedance, and bandwidth were measured and calculated.

Design goals for the 32x32 element array are:

•	Frequency	38.4 GHz
•	VSWR	Less than 1.5:1
•	Bandwidth	200 MHz
•	Gain	≥30 dB
•	Half-Power Beamwidth	$(2^{\circ}-4^{\circ}) \times (2^{\circ}-4^{\circ})$
•	Side-Lobe Level	<-20 dB
•	Efficiency	>50%
•	Size	5.5" x 5.5" x 0.25"

#### 2.2 ARRAY DESIGN

Initial work on the 32x32 element array was directed toward optimization of the basic radiating element and a 2x2 element array which was used as the "building block" for the final antenna. This 2x2 element array shown in Figure 2-1, was developed at a scale frequency of 3.07 GHz on 0.063" thickness Duroid 5880 substrate material. This scale frequency was chosen using the ratio of thickness of the available substrate material (0.063") to the

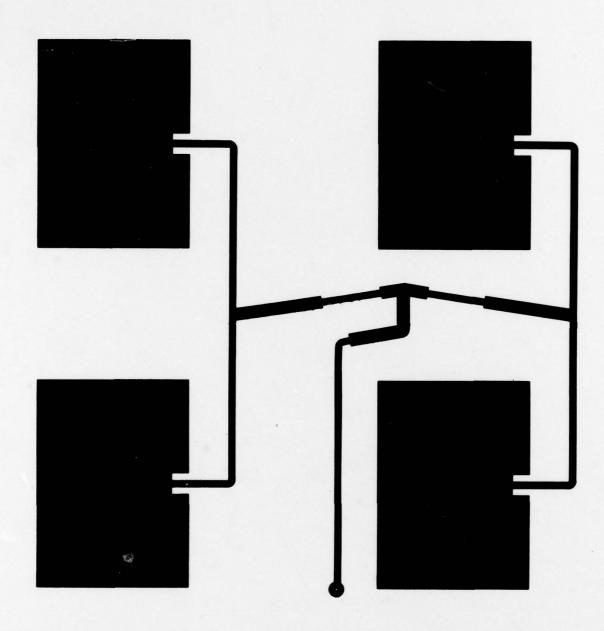


Figure 2-1 2x2 Element Array ( $\approx 1.6$  x actual size)

chosen thickness at the actual operating frequency (0.005"). This ratio, .005/.063 = 0.08 was then applied to the final design frequency (0.08 \* 38.4 GHz) to obtain the proper scale frequency (3.07 GHz). E and H-plane radiation patterns of the 2x2 element array are shown in Figure 2-2 and 2-3.

As part of the development process, a 4x4 element array (Figure 2-4) was fabricated and tested at a scaled frequency of 6.14 GHz on 0.031" thickness substrate material. E and H-plane radiation patterns for this array are shown in Figures 2-5 and 2-6. This array has a peak gain of approximately 18.0 dB with side-lobes down approximately -12.0 dB (standard case for a uniformly illuminated aperture).

Following is a brief analysis of array performance:

Theoretical Gain 10 $\log_{10} \frac{4\pi A}{\lambda^2}$	19.1 dB
Measured Gain	18.0 dB
Mismatch Loss (VSWR = 1.3:1) Actual Gain	0.1 dB 18.1 dB
Efficiency $\approx$ 19.1 dB - 18.1 dB $\approx$ 1.0 dB $\approx$ 79%	

This efficiency figure of 79% is commensurate with 4x4 element array results obtained during the previous contract.

A reduced side-lobe version of the previously discussed 4x4 element was designed, fabricated, and tested as the next step in the development process. The design for this array incorporated a -25 dB side-lobe Dolph-Tschebyscheff amplitude taper in both the E and H-planes. This amplitude taper is achieved by using the proper combinations of feedline impedances in the array corporate feed structure, as illustrated in Figure 2-7.

PART NO	3D72 GHZ	. NO 737 _k RANGE:	SERIAL NO UG SM.	OTHE
	DEVELOPMENT	PRE	FINAL	LJoine
PATTERN IN DE		CHART)= 0 DBI	SHEET _2	_ OF_2
340	350" 0-	10° 350° 20		
330		340		
30	111111111111111111111111111111111111111		330.	ĭ
320		RIAM	40.	
40	10-		320	
				50.
	1			310.
				60.
	200			30
				H
THATHATA				
HAHAMA	× 1 1 30,			曲曲
	475 SSSSSSSSSSSSSSSSSSSSSSSSSSSSSSSSSSSS			
†				
15 0 25	30 35	35 30 2	5 20 15 1	0 5 5
	30			
				1111
	25			14
				41
$\times \times $	200			12 240
				3
				230°
	10-			
15 220 140			140.	
210	5		150.	
150 200		160		
160*	190 180	170° 200	•	
	,,,,	130		
<b>2</b>				•
BALL BR	NOTHERS RESE	ARCH CORPOR		
		OLARIZATION E	E P RC	

Figure 2-2 E-Plane Radiation Pattern (2x2 element array, 3.07 GHz)

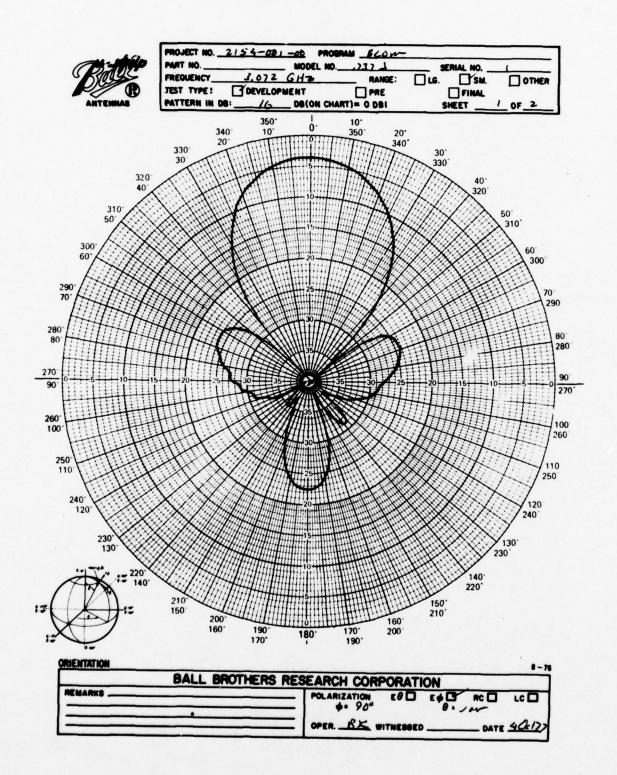


Figure 2-3 H-Plane Radiation Pattern (2x2 element array, 3.07 GHz)

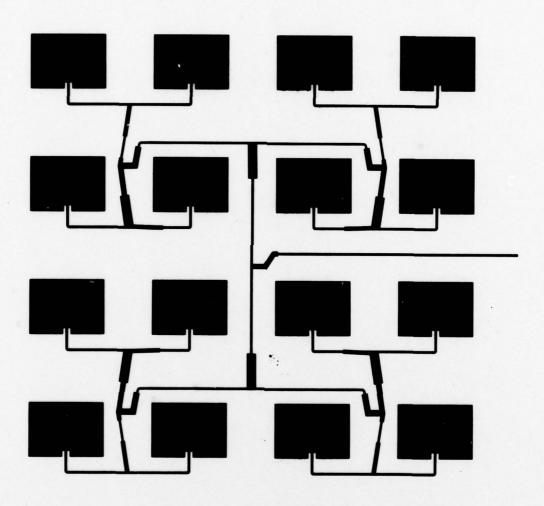


Figure 2-4 4x4 Element Array (6.14 GHz)

PART NO. FREQUENCY 6144 TEST TYPE: DEVELO PATTERN IN DB:	MODEL NO  DPMENT [ DB(ON CHART)=	RANGE:	SERIAL NO ] LG.	OTHER
PATTERN IN DB:	DRION CHAPTI-			
	DOLON CHART/	0 DB1	SHEET	OF
36.) 340 10	0 10	0 20		
· 20 T.T.	1	340		
330			30	
	Y 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	4-41/1/1/	1	
	$\langle \cdot   \cdot   \cdot   \cdot   N \rangle$	the last	320	
		11/1/	$\times / \searrow$	50°
		12		310
		AN	$\times$	3
//X/XI	11 11 11	11731	$\times \times \times$	60
$\times \times \times \times \setminus V \setminus V$			XXX	70
				290
THE XXIII	1	//	1	用單
The state of the s		1/		
THE K	3544///	1	HITTH	++++
- The state of			***************************************	
	C	30 25	20 15 1	0 5 0
1				
1			$H^{++}$	$++\downarrow\downarrow\downarrow$ ,
T X	4711 WX		444	2
XX ///	TITA	$\bigvee$	444	1
XXXX	11111111111111111111111111111111111111	$\langle \times \times \rangle$		1110
				250
$\times \times / \nearrow$	7111		$\times \times \times$	1/10
XXXI	(7 / 1   1   1   1   1   1   1   1   1   1	1740		240
CALITY	41111	1117	$\wedge \wedge \wedge \wedge$	1
XINII	111111	174		230
	1-1-1-1-1	1111		
V//-LI		1.4.	140	
210		THE	. 1	
160 200		160	210	
160 190	180 17	0 200		
170	, 19	Ю		
				8 - 76
BALL BROTHER	S RESEARCH	CORPORAT	ION	
X4 ARRAY	POLARIZA	TION ER D	HE ALL RC	_ rc _
				ATE 10/31/77
	210 150 206 160 190 170	BALL BROTHERS RESEARCH  SEA ARREST  POLARIZA  POLARIZA	210 150 150 150 150 150 150 150 160 170 180 170 200  BALL BROTHERS RESEARCH CORPORAT  184 4 AREAS  POLARIZATION  \$ ε θ Ε   \$ 90 • Ε Θ Ε   \$ 90 • Ε Θ Ε   \$ 100 150 150 150 150 150 150 150 150 150	30 30 310 40 320 40 40 320 40 40 320 40 40 40 40 40 40 40 40 40 40 40 40 40

Figure 2-5 E-Plane Radiation Pattern (4x4 element array, 6.14 GHz)

	PROJECT NO. 2154		PROGRAM ECO		Ma	
(Day)	PART NO	6144	MODEL NO	DANCE:	SERIAL NO	
	FREQUENCY_	DEVELOPME	NT I	RANGE:	Ø.LG. □ S	
ANTENNAS	PATTERN IN		DB(ON CHART)		SHEET	OF
		350	0 10			
		140 10	35	0 20		
	330		1	16de	30	
320	1	in Authorities	T i X	-1 $I$ $I$	1.1	10-
40		( V )	1	1 17		20
310		141		1		50
50				17		310
200	$\times \times \times$	77411	11111	10	$/\times/>$	( ) eo
300	$\bigvee$		10111	11/1		260
		I XXI		XV	$\times \times \times$	
290		XII	1-25-1			70
70		111	11117	1		290
	THIK		think?	1	1	1
80	4447			1	1	80
	HHH			1	1111111	
	t + t + t = 0			4		
		1-1-1-1		-		2
H-111111111111111111111111111111111111	++++			Z	77714444	
00	+			XX		10
"     T	TY	$\times$ // $\times$	414	XX	ALL THE	4 10
250		1741		$\langle X \rangle \rangle$		110
110		$\times$ / $\uparrow$	###	/X		1250
	$\times / \times /$	7.1		1		
240			TOTAL	1174		240
X		1711		++1	$\times \times $	X /
230		4/11		1		130
130	/ */	17+1	1 1 1	-	1.4.1	7 250
1220	V//			1.1.	1	40
178	210	17-1-		11	150	.0
( )	150	4/1/			210	
X		60 190	180		)	
		170	1	90		
ORIENTATION						8 - 76
	BALL	BROTHERS I	RESEARCH	CORPO	RATION	}
REMARKS 4x			POLARIZA		Bes CB	WC
					Mail	
			OPER. B	WITH	ESSED	_ DATE OFSIT

Figure 2-6 H-Plane Radiation Pattern (4x4 element array, 6.14 GHz)

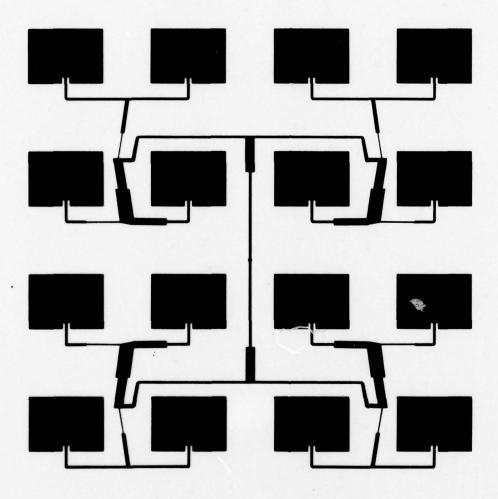
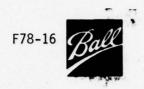


Figure 2-7 4x4 Element Reduced Side Lobe Array (6.09 GHz)



Measured E and H-plane radiation patterns of this array are shown in Figures 2-8 and 2-9. As can be seen, the side-lobe level in both cases is well below the design value of -25 dB.

Following is a brief analysis of array performance:

Theoretical Gain	19.1 dB
Measured Gain	17.2 dB
Aperture Efficiency (Loss due to amplitude taper)	0.6 dB
Mismatch Loss (VSWR = 1.9:1)	0.4 dB
Actual Gain	18.2 dB
Efficiency $\approx$ 19.1 dB - 18.2 dB $\approx$ 0.9 dB $\approx$ 81%	

A -25 dB side-lobe Taylor taper (which is similar to the Dolph-Tschebyscheff) was chosen for the 32x32 element array. Rather than applying the amplitude taper to every element, it was applied to the previously mentioned 2x2 element "building blocks". A computer evaluation of this approach shows very little degradation over amplitude variation in every element. Figure 2-10 is a representation of the final 32x32 element array configuration.

#### 2.3 WAVEGUIDE FEEDPLATE DESIGN

When contemplating an array of this magnitude (1024 elements) in the millimeter wavelength region, at least three problems become immediately evident.

(1) In general, the length of feedline from the input connector to any element in a corporate fed antenna is equal to onehalf the sum of the length and width of the array. Therefore, as an array grows in size (number of elements), there is a corresponding increase in the feed system losses.

Royce	PART NO FREQUENCY_	600	MODEL NO			ERIAL NO	
	The state of the s			RANGE:	Mrc.	SM.	OTHER
ANTENNAS	TEST TYPE:	DEVELOPE 17.4	_ DB(ON CHART)	PRE O DBI		FINAL SHEET	OF
		350 40 10		0 50 20			
	330			17	33		
320° 40′		( X )		TY		320	
310	$\times / /$	1		1	//	$\langle \rangle$	50
300		11		1/	X		60
60	$\times \times$	7/1/-	tith	12/		$\times$	300
		$\times 1$	+++	1/X	X		+-7
HIH	THA!	$\times \gamma$	11/1	XX	X	17	工具
		1	3	XX	+	計当	
10000				1			
				##	+++		<b>1</b>
	1-1-	XXIII		XX	#		
	1	////	7111	XX	XX.	1	47
0		$\times 11$	<b>##</b> **			X	1-7:
240	$\times\!/\!/$	47/	1-1-1-1				120
230		1744	4444	+11	X		130
130	141	7+11	4114	1			230
220	17	7-11		+++		140 220	
1:	210 150 20	00		160	15 21	0	
	16	0 190 170	180	70 200 90			
RIENTATION							8-
	BALL	BROTHERS	RESEARCH				
REMARKS	LOW	SIDELOGE	POLARIZA	TION E	E	# RC [	_ rc

Figure 2-8 E-Plane Radiation Pattern (4x4 element reduced side lobe array, 6.09 GHz)

-u- edda	PROJECT NO. 215		RAN ECC		
C RONUE	PART NO	MODEL NO.	RANGE:	SERIAL NO SM.	OTHE
P	TEST TYPE : Q DE	VELOPMENT	PRE	FINAL	C o the
ANTENNAS	PATTERN IN DB:	7.4 DBION CHA	RT)= O DBI	SHEET	OF
	340	26.0	10" 350 20		
	20	-	350 20	)*	
	330		X dillo	30	
320		Attitute	1	100	
40	1 1 4 1		1 X Try	320	
1			1-11/		
3	Jan		V		50°
		19-1-1	1/7	XXXX	310
X			11/		60
X	$X \setminus X \setminus X$	11-1-10-4	1/1/1/		300
X	XXXXXX	1	11/1		
4		(1) Linkely	11/1/		1
174	XXX	ATTHE	14/		1
1-4	7/08/	4/1/1/	In		
41	4011	The state of the s		11	4
11	744-		1X	-1-1-1	4
1:17	1+11-11				
	1111 1 1 1 1 1 1	THE WAR	30 1 2	20 15 16	5
		ZXIII X			
1	JULY JULY	X	TY XII	+UHHIIHH	+4.0
-11	1	XVIIIIIII	XXX		UUIII
+	Mark No	1111		HAHA	1/
1	XXXX	1/1/11/11	11/3	CANAL A	7
1	XXX	11-1-	1 / X		1
X	(/)//	1 1 1 1 1 1	Litter	$\times \times \times >$	1
X	NYXX	17110-1	THE		120
X	1X/1/		177		240
20	X/X///	77-1-1-1	-1-1-1-1	XXXX	/130
1	11/1/1		1 1 1		130
1	1/1/	7-1-1-1-1	++1		
#5 220 \ 140	VIVI		Till I	140	
	1/1/		1	1.1.7	
-12	210		1 1	150 210	
1	200	190	160		
	160	190 180	170° 200		
	DALL DOCTU	EDE DESEAD	NU CORDO	PATION	8-
		ERS RESEARC	CH CORPOR	KATION	1 100
	1x4 Low Si	DELOBES	PER PO	BE BE ROLL  B: WOLL  B: WOLL	
		0050	MW WITH	MW .	- D/a/
		- OPER	WITH	SOLU DA	IS TIME

Figure 2-9 H-Plane Radiation Pattern (4x4 element reduced side lobe array, 6.09 GHz)

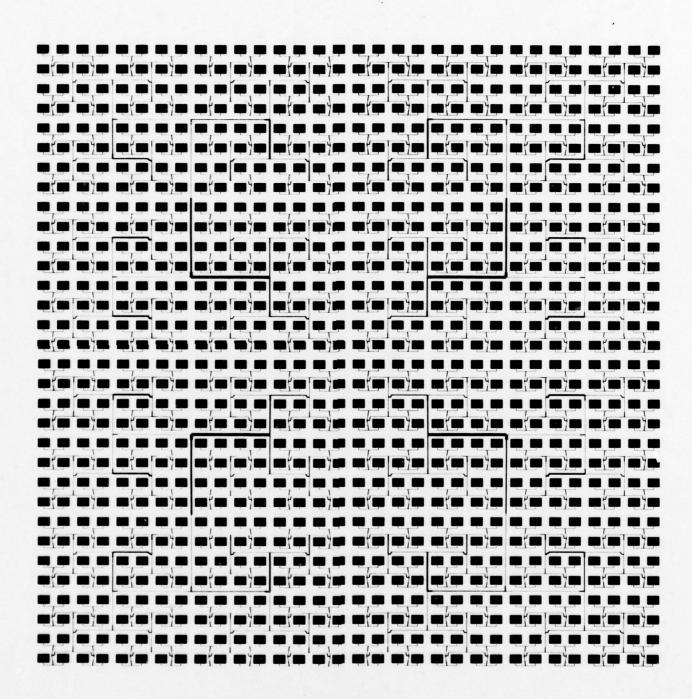


Figure 2-10 32x32 Element Reduced Side-Lobe Array (38.4 GHz)

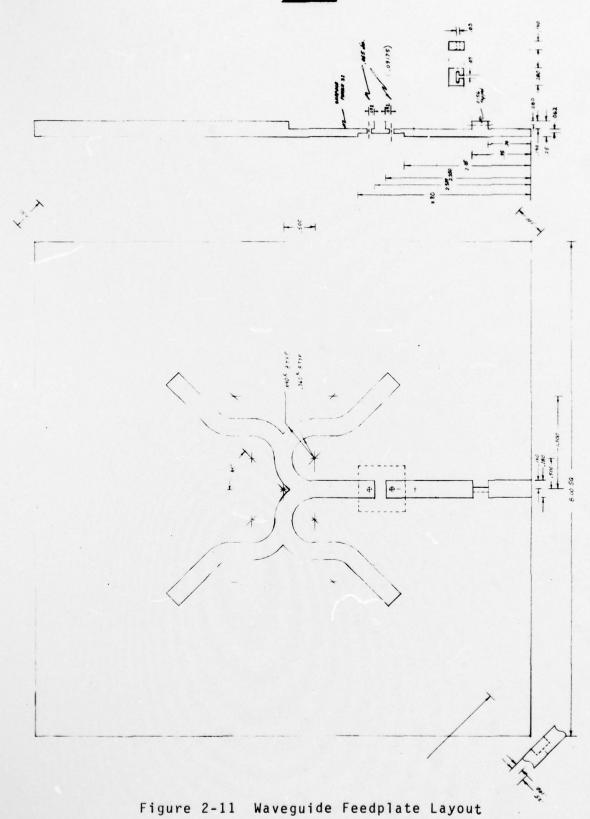
- (2) For the 32x32 element case, the power level in the two feedlines leaving the input connector is approximately 27 dB above the power level received by adjacent radiating elements. This power difference is of the order of magnitude of coupling between a radiating element and an adjacent feedline. The effect of this coupling is to disrupt amplitude and phase relationships in elements adjacent to these primary feedlines.
- (3) Since the array substrate material is flexible and only 0.005" thick, it requires some type of backing plate for both support and to maintain array flatness.

The waveguide backplate, or feed plate, has been incorporated as a solution to all three of the above mentioned problems. The basic support plate referred to in (3) was chosen to be aluminum of approximately 0.25" thickness. This thickness allowed a four-way power divider to be milled into the plate in waveguide. A drawing of the feed plate layout is shown in Figure 2-11.

In effect, the first two levels of feed system power division have been converted from microstrip to waveguide. The array itself is now divided into quadrants, each of which is fed from one leg of the waveguide power divider.

This approach has the following immediate advantages:

- (1) Approximately 3.4" of microstrip feedline have been replaced with waveguide. Loss is approximately 0.60 dB/in in microstrip versus less than 0.02 dB/in in waveguide. This results in a loss reduction of nearly 1.3 dB.
- (2) Primary feedlines up to the third level power dividers have now been removed from the array, nearly eliminating problems with radiating element/feedline interactions.



20



## (3) The array substrate is provided with a rigid, flat support.

To accommodate development and testing, the array substrates delivered as part of this contract were glued to a 0.063 thick aluminum plate which was drilled and tapped so it could be screwed to the waveguide feed plate. This allowed relatively easy separation of the array from the feed plate. In future models the array substrate would be glued directly to the waveguide feed plate.

#### 2.4 TEST RESULTS

Before fabrication of the final 32x32 element arrays at 38.4 GHz, a scaled version of the entire array was fabricated and tested. The array was etched on 0.014" thickness polyguide (similar to the Duroid substrate) and operated at 13.8 GHz.

E and H-plane radiation patterns of this array are shown in Figure 2-12. Side-lobe levels nearly meet the -20 dB design goal in both planes. It should be noted that this array did not have the waveguide-type feed system, but was fed entirely with a microstrip corporate feed network. Measured gain of the entire array was 24 dB. This low value was later discovered to be the result of a bad test cable. The gain measurement could not be repeated as part of the array feed system had been removed to perform tests on one-half of the array.

Figure 2-13 shows E and H-plane patterns for one-half (16x32 elements) of the array. In this case, measured gain is 28.0 dB for one-half the array.

Following is an analysis of array performance:

Theoretical Gain	38.0	dB
Measured Gain (½ array)	28.0	dB
Other Half of Array	3.0	dB
Aperture Efficiency	0.9	dB
Mismatch Loss (VSWR = 2.0:1)	0.5	dB
Actual Gain	32.4	dB
Efficiency ≈ 38.0 dB - 32.4 dB ≈ 5.6 dB ≈ 28%		

TEST TYPE:   DEVELOPMENT   PRE   FINAL   SHEET   OF
330 330 330 330 330 330 330 330
336 30 30 30 30 30 30 30 30 30 30 30 30 30

Figure 2-12 E and H-Plane Radiation Patterns (32x32 element array, 13.8 GHZ)

PROJECT NO	2154	PROGRAM	COM SERVINO	
FREQUENCY	13.80 €	RANG PRE ON CHART)= 0 DBI	FINA	I. OTHER
34	350 0 10	19	20 340	
330 30		\\ <b>\</b> = \( \cdot \)	300 330	
40	1	E-12	32	
	1111	h//		310
		#h/		300
	MA	IMA		
	11	11/		
10			25 20 15	
711				11
	44	44		240
	411	H-AA	ave X	130
15 220	1111	1111	14/	)
210 100 200			150 210	
160		1,1	2( <b>x</b> )	
		120	200	

Figure 2-13 E and H-Plane Radiation Patterns (16x32 element array, 13.8 GHz)



Figures 2-14 and 2-15 are front and back views of the final array operating at 38.4 GHz. Two units (Model AN152A, Serial Numbers 001 and 002) were delivered. Input VSWRs of the two antennas are presented in Table 2-1.

Table 2-1
INPUT VSWRs OF MODEL AN152A
SERIAL NUMBERS 001 and 002

Freq (GHz)	Serial #001 VSWR	Serial #002 VSWR
38.340	2.50:1	1.53:1
38.355	2.25:1	1.51:1
38.370	2.15:1	1.55:1
38.385	2.10:1	1.55:1
38.400	2.00:1	1.60:1
38.415	1.97:1	1.64:1
38.430	1.95:1	1.67:1
38.445	1.95:1	1.71:1
38.460	2.00:1	1.78:1

Measured E and H-plane radiation patterns of Serial Numbers 001 and 002 at frequencies of 38.0/38.1, 38.4 and 38.7 GHz are shown in Figures 16 through 27. Gain values for S/N 001 and 002 at 38.4 GHz are 29 dB and 25 dB respectively.

Although the measured gain of S/N 001 nearly meets the design goal, side-lobe levels do not approach the -20 dB goal. When S/N 002 was first tested, general pattern shape and side-lobe level was much worse than S/N 001. The radiation patterns shown in Figures 2-22 through 2-27 are the result of an attempt to "retune" the array by placing pieces of teflon tape on certain parts of the feed structure. The tape effectively changes the impedance and phase relationships of the feed network. As can be seen, this "retune" had the effect of achieving the desired pattern in the H-plane.



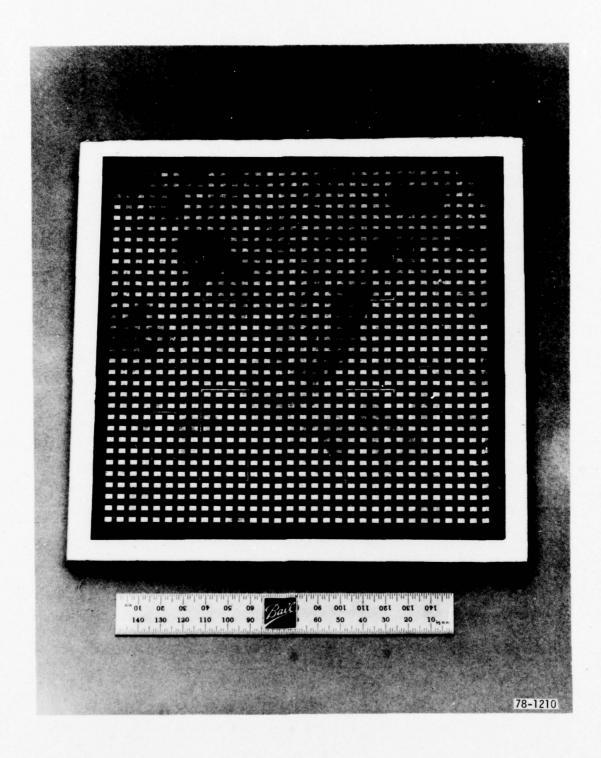


Figure 2-14 Front View of 32x32 Element Reduced Side Lobe Array (38.4 GHz)



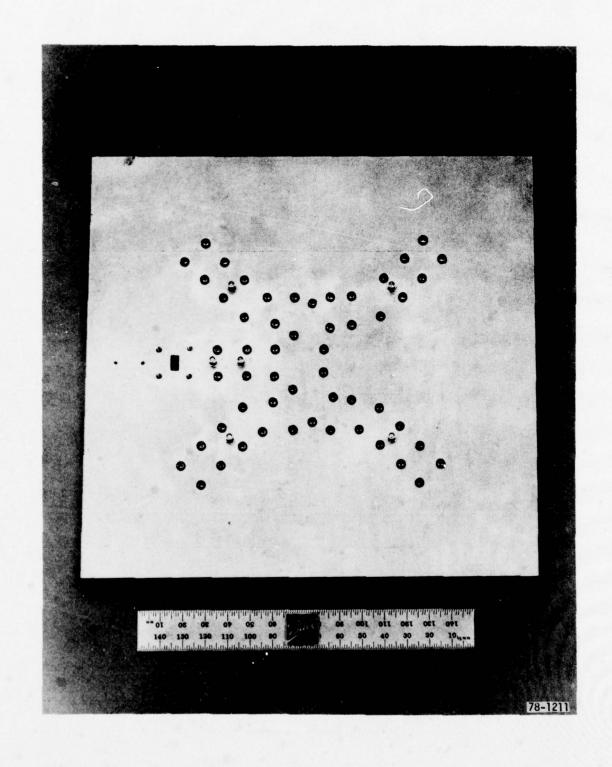


Figure 2-15 Back View of 32x32 Element Array (38.4 GHz)

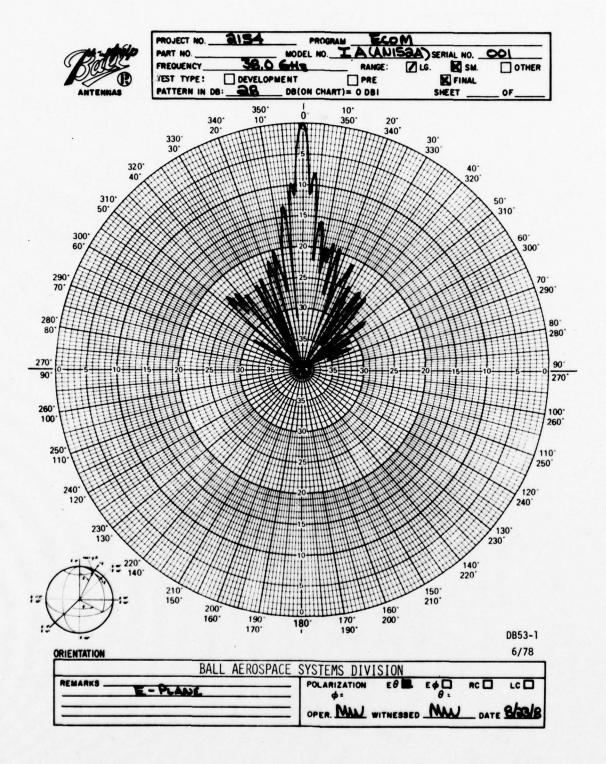


Figure 2-16 E-Plane Radiation Pattern (Serial #001, 38.0 GHz)



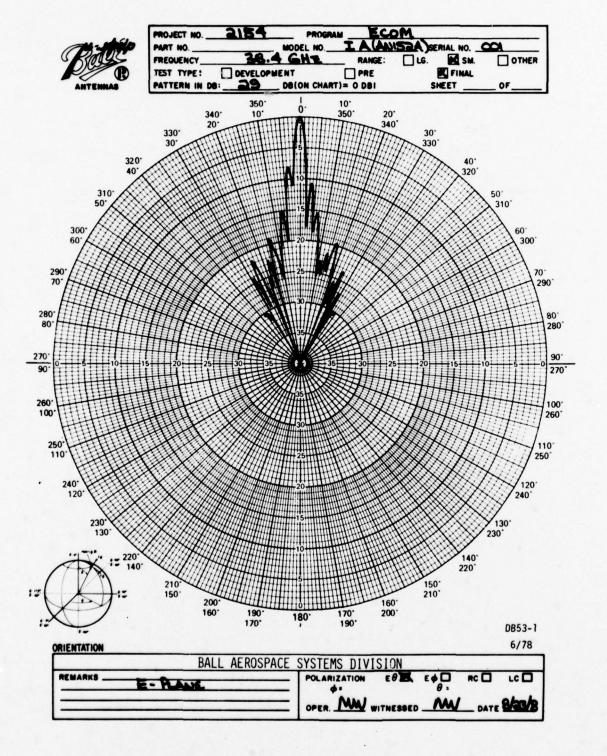


Figure 2-17 E-Plane Radiation Pattern (Serial #001, 38.4 GHz)

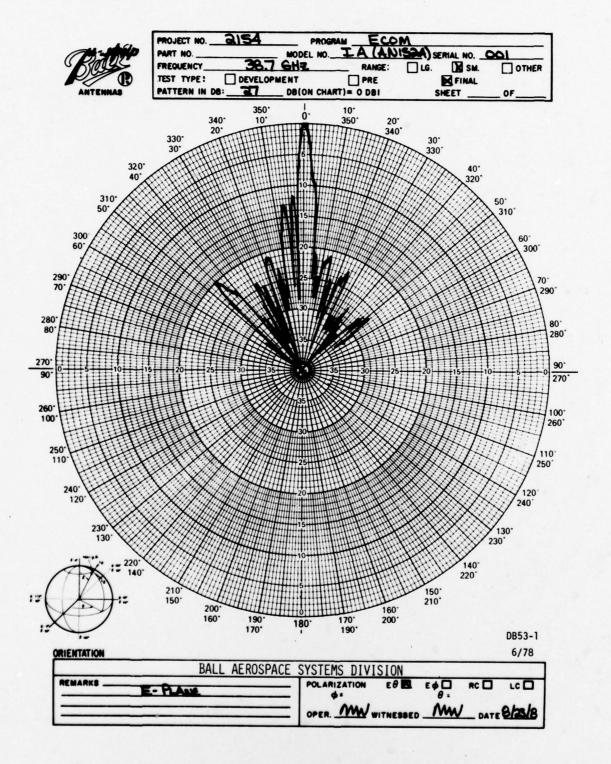


Figure 2-18 E-Plane Radiation Pattern (Serial #001, 38.7 GHz)



ملاقهد الم	PROJECT NO. 2154 PROGRAM ECOM PART NO. MODEL NO. I A (ADISA-A)SERIAL NO. COI						
0000	FREQUENCY		CHE	RANGE:	LG.	M SM.	OTHER
B	TEST TYPE:	DEVELOPM		PRE	8	K SM. FINAL	
• [	PATTERN IN DB:		_ DB(ON CHAI		SHE	ET	OF
	340-	350°	0.	10° 350° 2	0*		
	330. 20.	THEFTER	A	34	30.		
	30.	油油油	5		330.		
320"						320	
40.			10			320.	
							50° 310°
			15				310.
							60.
			20				300
HAX							
4774		833434E	25				
	HAHA				XXXX		
		XXXXX					
1111111				XXX	H		
	4447711111						
1015-	20 25	30 35-	<b>第伊</b>	5 30	25 20	1510	5
	111111				HHH	IIIIII	
HIIII							
			300				
						27	1
	$\times \times \times \times$					THE	1
	X				<b>****</b>		120
	XXXX						120 240
			15				A .
30			########				130.
			10				230
12 220	ZHATHALL				HARAITE	140° 220°	
1	210		5		Hilliam	220	
+:=	210° 150°				150.		
1	200° 160°	190	11116111111	170 20	0.	20.	
		170	180-	190			DB53-1
							6/78
	RΔII	AFROSPA	CE CVCTE	AS DIVISI	ON		0/76
		ALNOSTA				A RC	l LC 🖸
H-1	LAIR		-   (	b =	0		
			OPER.	MW WITH	ESSED M	W_ DA	TE 8/00/E

Figure 2-19 H-Plane Radiation Pattern (Serial #001, 38.0 GHz)

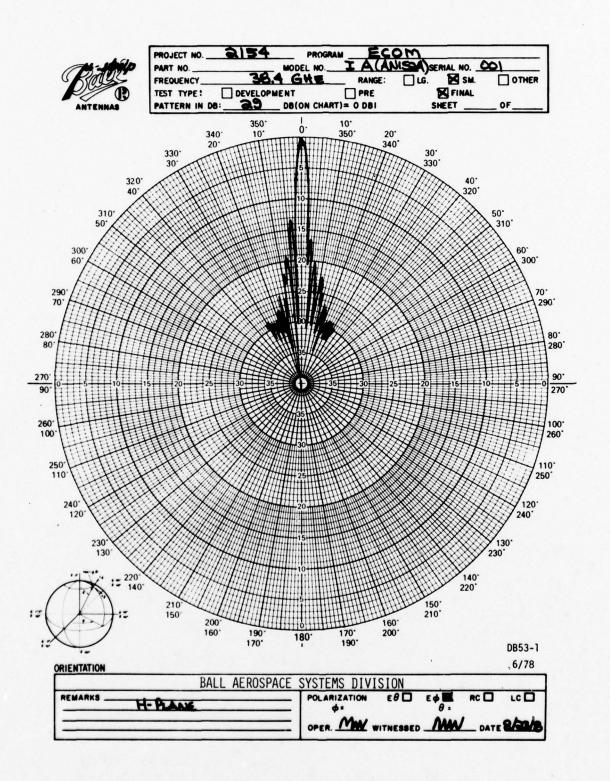


Figure 2-20 H-Plane Radiation Pattern (Serial #001, 38.4 GHz)

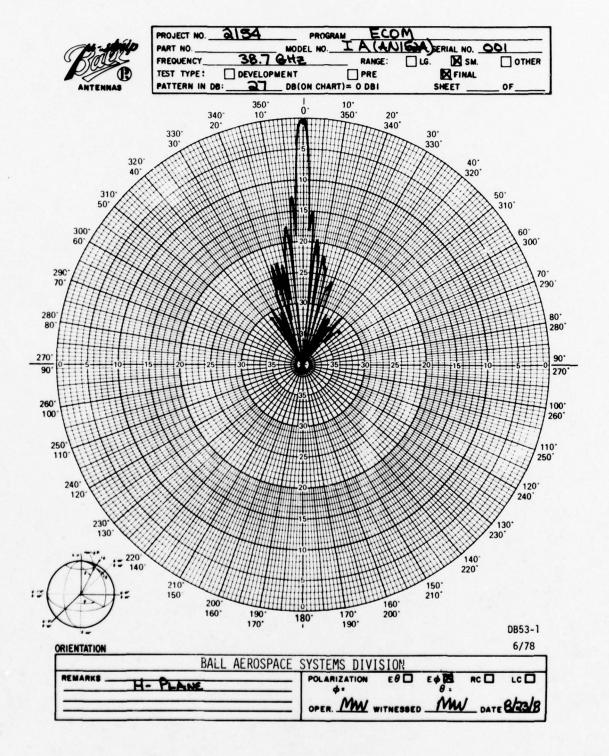


Figure 2-21 H-Plane Radiation Pattern (Serial #001, 38.7 GHz)

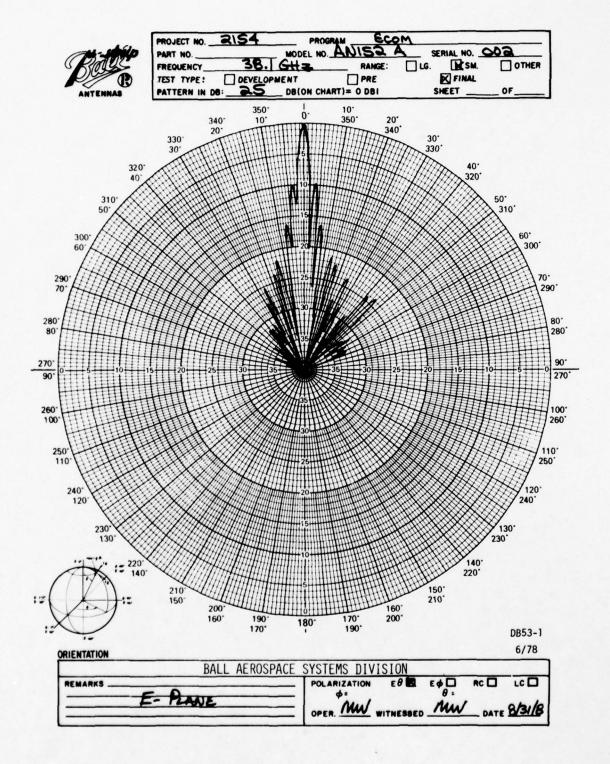


Figure 2-22 E-Plane Radiation Pattern (Serial #002, 38.1 GHz)

10		2154		COM		
(D) Tolly	PART NO.	38.4	MODEL NO. ANIS		RIAL NO. C	
0)000	FREQUENCY			IGE: LG.	⊠ sm.	OTHER
	TEST TYPE! [PATTERN IN DB:	DEVELOPMI	ENT PRI DB(ON CHART)= 0 DE		FINAL EET	OF
ANT CHINA	CHITCHIN IN BOT					
	340-	350°	0. 10.	20°		
	20.			340		
	330.	THHHH!		30°		
	CA THAT HIS		5			
320 40°		ETHER THE			320	
			10			
310.						50*
30/			is the state of th		XXXX	310
300°					*****	60.
60.	*******		20			300.
290			25	<b>X</b>		70
290 <sup>-</sup>						29
			H 130 H		HIII	開開
0.						
)						
10 10					15	
0.[7]						
HILLIE		<i>XXXXX</i> XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX	30			
250						11
110			25			250
	***					
120			20		$\times\!\!\times\!\!\times$	120
- W					$\times\!\!\times\!\!\times$	
230			15			130.
130						130.
	ZO TO SHELLING		10-110-11		XXX	
140					140	
12/	WHITHIII		5	111111111111111111111111111111111111111		
1:	210°			150 210		
X	200° 160°	190	190: 170:	160° 200°		
	100	170	180.	200		DB52.1
						DB53-1
ORIENTATION						6/78
		AEROSPA	CE SYSTEMS DIV			
REMARKS	E-PLANE		POLARIZATION	<b>Ε</b> θ <b>Ε</b> Φ <b>Ε</b> φ	RC C	
			- Mari	WITNESSED 1	Aul	8/21/0
			- OPER TOWN	WITNESSED	DA	TE 0/3//5

Figure 2-23 E-Plane Radiation Pattern (Serial #002, 38.4 GHz)

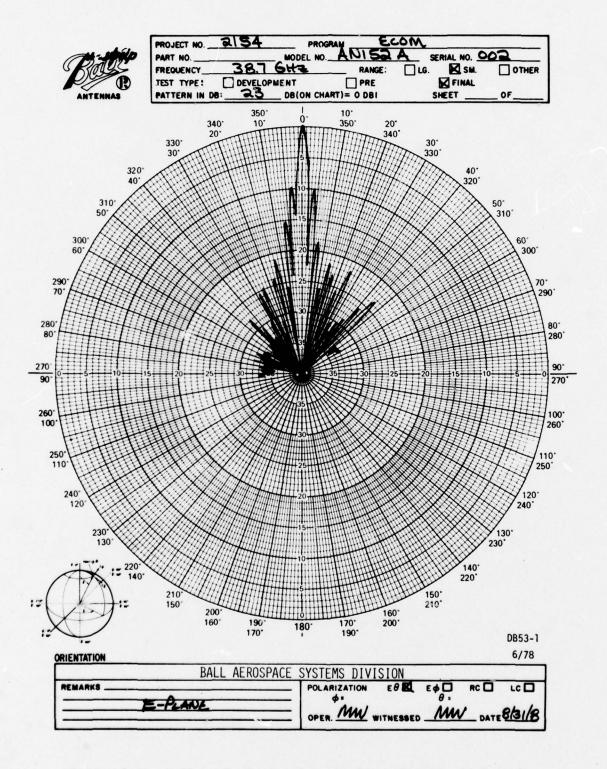


Figure 2-24 E-Plane Radiation Pattern (Serial #002, 38.7 GHz)

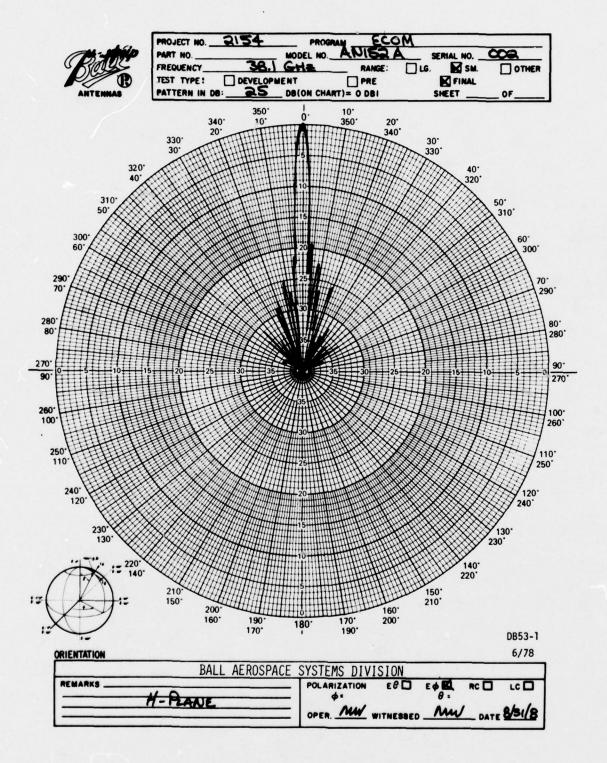


Figure 2-25 H-Plane Radiation Pattern (Serial #002, 38.1 GHz)



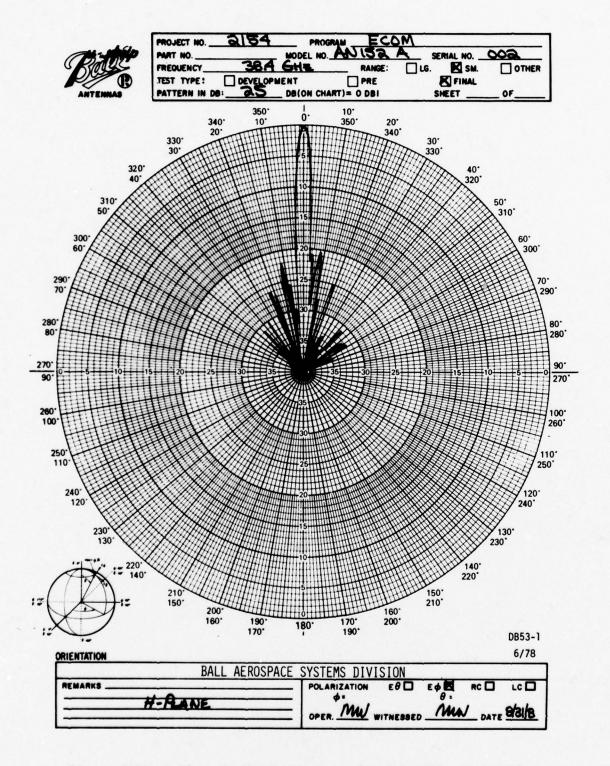


Figure 2-26 H-Plane Radiation Pattern (Serial #002, 38.4 GHz)

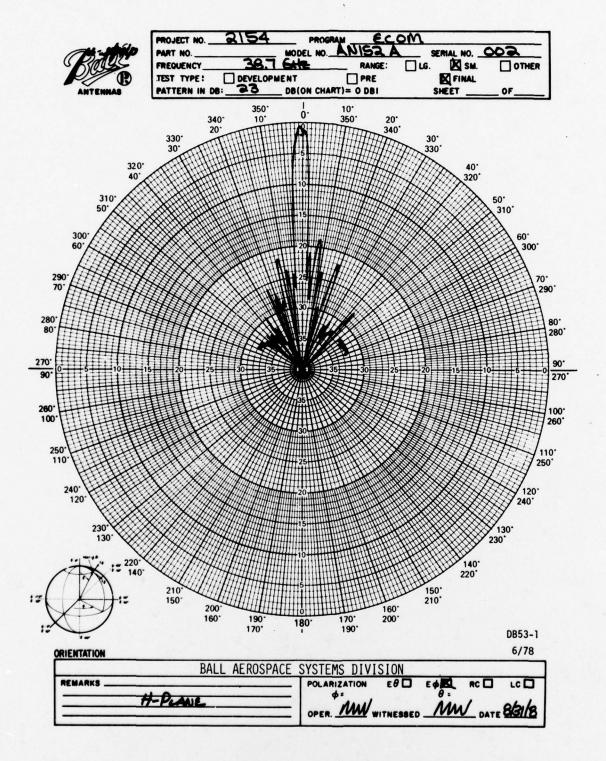


Figure 2-27 H-Plane Radiation Pattern (Serial #002, 38.7 GHz)



Similar problems (and results) were encountered with the arrays fabricated for the front-end mixer integration portion of this study. A considerable amount of time was spent investigating the problem with the final conclusion being that the problem appeared to be caused by non-uniform substrate material. Variations in either substrate dielectric constant or thickness would cause an imbalance in the phase and amplitude relationship between the array elements. Some semblance of the proper conditions could be achieved by selected tuning (or detuning) of portions of the array; however, the power lost in these detuned areas is evident in the reduced gain level in S/N 002.

Following is a summary of array performance:

Theoretical Gain	37.7 dB
Measured Gain (S/N 001)	29.0 dB
Aperture Efficiency	0.9 dB
Mismatch Loss (VSWR = 2.0:1)	0.5 dB
Actual Gain	30.4 dB

Efficiency  $\approx$  37.7 dB - 30.4 dB  $\approx$  7.3 dB  $\approx$  19%

As previously mentioned, it is believed that a considerable portion of the 7.3 dB loss resulting in the low efficiency can be attributed to mismatches within the feed system. The antenna system loss budget shown in Table 2-2 gives an indication of the amount of power apparently lost in these mismatches.

Some of this 3.7 dB unexplained loss may be attributed to such things as non-uniform phase distribution on the radiating elements; however, it is believed that the majority of this number may be attributed to mismatch losses within the feed system caused by a non-uniform substrate.

# 2.5 32x32 ELEMENT ARRAY SUMMARY

Table 2-3 summarizes the performance parameters of S/N 001 and 002.



# Table 2-2

# LOSS BUDGET S/N 001 (38.4 GHz)

Measured Gain	29.0 dB
Feedline Losses (≈0.6 dB/in* 3 in)	2.0 dB
Aperture Efficiency	0.9 dB
Waveguide Loss (≈15 dB/100 ft)	0.1 dB
Waveguide Power Divider Loss (2)	0.4 dB
Waveguide/Microstrip Transition Loss	0.3 dB
VSWR (2.0:1)	0.5 dB
Radiating Element Efficiency (≈80%)	_0.8 dB
TOTAL	34.0 dB
Theoretical Gain	37.7 dB
Difference	3.7 dB

F78-16 Ball

Table 2-3 SUMMARY OF ARRAY PERFORMANCE (AN152A)

S/N 002	38.4 GHz 1.6:1 >200 MHz (Pattern) 25 dB 2.5° x 2.5° -10/-12 dB <-20 dB 7%	8.0" × 8.0" × 0.32"
S/N 001	38.4 GHz 2.0:1 >200 MHz (Pattern) 29 dB ≈2.4° x 2.3° -8/-11 dB -13/-17 dB 19%	8.0" × 8.0" × 0.32"
Design Goal	38.4 GHz Less than 1.5:1 200 MHz ≥30 dB (2 <sup>0</sup> -4 <sup>0</sup> )×(2 <sup>0</sup> -4 <sup>0</sup> ) -20 dB ≥50% ≥50%	5.5" X 5.5" X 0.25"
Parameter	Frequency VSWR  Bandwidth  Gain  Half-Power Beamwidth  [Side E-Plane  Lobe  Level H-Plane  Efficiency	Size



# Section 3 RECEIVER FRONT-END CIRCUIT

#### 3.1 SYSTEM DESIGN

The microstrip antenna receiver front-end circuitry is shown in block diagram form in Figure 3-1. This is a "typical" front-end design and was chosen for

## MICROSTRIP ANTENNA

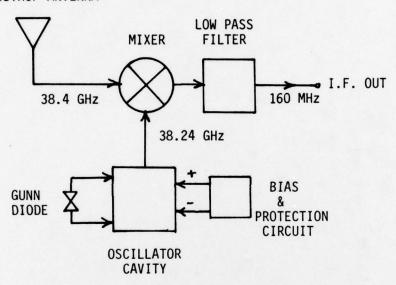


Figure 3-1 Antenna Receiver Front-End Block Diagram

its simplicity. The antenna itself forms the preselect filter and the signal is therefore band limited by the antenna and mixer combination only. The oscillator frequency is chosen to be 160 MHz below the antenna center frequency in order to produce an IF center frequency of 160 MHz. The output frequency is band limited only by the cabling and any subsequent circuits at the output of the mixer. The oscillator output is of such a level as to produce "saturation" of the Schottky-barrier mixer diodes. The frequency of operation for the oscillator is adjustable by means of a quarter-wave sliding short circuit and a mode suppressing screw. There is also some adjustment possible by varying the bias voltage to the oscillator. Figures 3-2 and 3-3 are front and rear views of the antenna-receiver system in its final form.



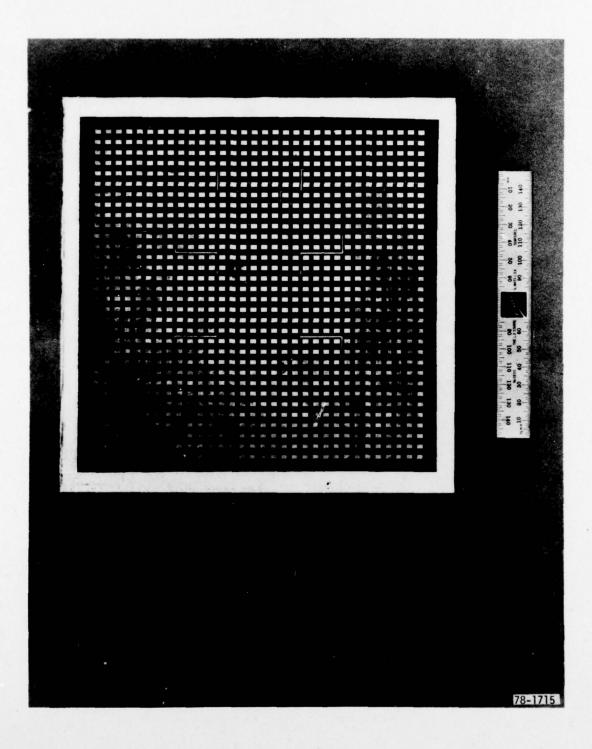


Figure 3-2 Antenna-Receiver System (Front View)



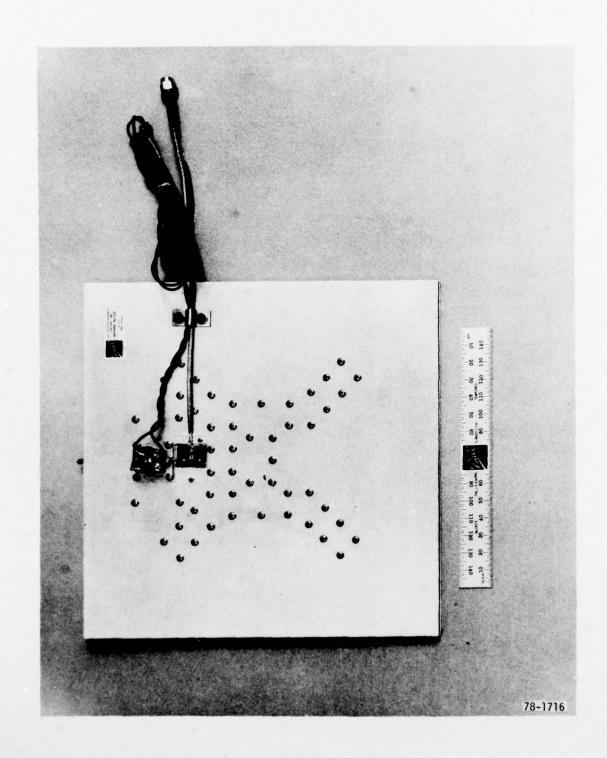


Figure 3-3 Antenna-Receiver System (Rear View)

## 3.2 GUNN EFFECT OSCILLATOR

The oscillator is a Gunn-effect diode oscillator. The diode is a Varian VSA9210S3 type in a stud-mount package. The diode is placed within a resonant cavity and voltage is applied. The present theory of operation is understood to be that a negative resistance is produced by a sudden change (decrease) in carrier mobility with increasing voltage (field strength). The frequency of oscillation is determined by the effects of the resonant cavity (its impedance) and the impedance of the diode itself.

The initial approach to the Gunn effect oscillator was a microstrip design. This type of circuit was used because it offered simplicity of design and ease of circuit change. The circuit is shown in diagram form in Figure 3-4.

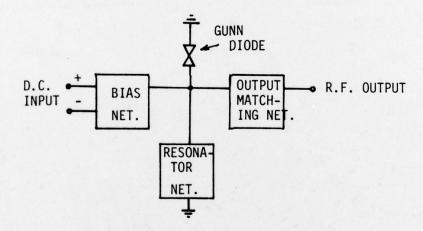


Figure 3-4 Gunn Oscillator Diagram

This is essentially the same as that used for the waveguide design. The circuit consisted of three basic parts: The biasing network, the output matching circuit and the resonator network.

The biasing network was dictated in part by the operating instructions from the manufacturer. This network consisted of a Zener diode for overvoltage



protection, a shunt capacitor for low frequency "spike" suppression and an R-C entwork for high frequency (>7 MHz) suppression. The output of this network was fed to the oscillator cavity (or resonant circuit) by way of a low-pass network (shown in Figure 3-5). This network is merely two pairs

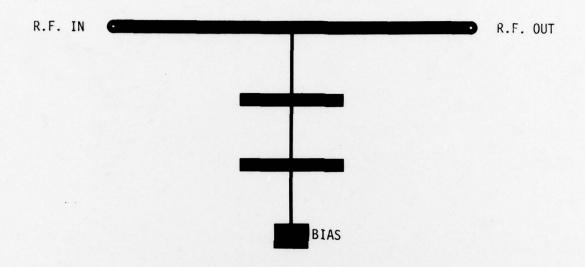


Figure 3-5 Microstrip Oscillator Low-Pass Filter Circuit

of open quarter-wavelength stubs, spaced one-quarter wavelength apart. Tests have shown this network to provide greater than 20 dB of suppression at 38 GHz. This network in turn is connected to the output line  $(50\Omega)$  and is spaced more than a wavelenth away from the output of the oscillator and from the resonant circuit.

The Gunn diode and resonant circuit consist of a  $\lambda/2$  wavelength resonator and a  $\lambda/4$  matching transformer (see osc. layout, Figure 3-6). The resonator

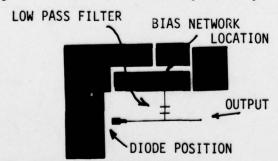


Figure 3-6 Microstrip Oscillator Layout Configuration



itself is less than  $\lambda/2$  wavelengths wide and as such tends to suppress "moding" in the oscillator by disallowing the possibility of oscillations in the orthogonal direction of the microstrip patch. As is, the oscillator had a tendency to oscillate at a frequency near the required due to dual responses from the interaction of the matching transformer and the resonant circuit. Figure 3-7 is a computer printout based on the circuit model used for the microstrip case.

Frequency (GHz)	Impedance (Magnitude & Angle)				
P1	P2	21	2 77		
45.00 44.00	1.00	17.51 18.31	-1.62	44.37	GHz
43.00 42.00	1.00	19.87 22.31	-6.01 -10.33		
41.00 40.00	1.00	25.83 30.62	-14.40 -17.83		
39.00	1.00	36.74	-19.95		
38.33 37.00	1.00	43.76 50.42	-19.80 -16.61		
36.00 35.00	1.00	54.76 55.38	-10.67 -3.84		CII-
34.00 33.00	1.00	52.69 48.37	1.56	34.29	GHz
32.00	1.00	43.97	4.69		
31.30 30.00	1.00 1.00	40.36 37.85	3.30 0.90		

Figure 3-7 Computer Printout of Oscillator Output Impedance (Z1)

Wherever the output impedance (Z1) becomes real, a possibility of oscillation exists. The actual point of oscillation is greatly dependent on current as the diode negative resistance can vary over a fairly wide range. This circuit could be coarsely tuned by screwing the diode inward or outward from its mounting bracket, thus effectively increasing or decreasing the resonant cavity length. This method of tuning had the added feature of providing a small capacitance (a very short, open stub) in parallel with the diode.

The output circuit was to feed the mixer circuit directly such that the only waveguide probe was at the signal input to the mixer. Since the diode impedance was guite low (of the order of a few ohms), a matching transformer



(or transformers) was necessary. Thus, a one-quarter wavelength line was added between the diode resonator and the output  $50\Omega$  line. This line width (and thus its characteristic impedance) was determined experimentally and was of the order of 20 ohms.

The final configuration is shown in Figure 3-8. In this case, the diode has been placed in the center of the waveguide and is biased by means of a sliding "slug" type low-pass filter. The frequency of operation is determined by the radial line formed at the end of the "slug". This radial "cavity" is tuned by changing the separation between the radial cavity end and the bottom of the waveguide. This is accomplished by screwing the diode in or out and changing the fringing field capacitance at the edges of the radial line. This separation varies from a minimum of about 5 mils (0.005 in) to about 15 mils (0.015 in). This allows a tuning range of several GHz and provides a method of "rough" or coarse tuning. The diode may also be tuned by adjusting the DC voltage. This method provides a more fine tuning capability. Coarse tuning can also be accomplished by means of a "sliding" short at one end of the waveguide, but as this can also result in "mode-slipping", that is, the sudden discontinuous change in frequency with tuning, it is not recommended. The frequency and model stability can also be changed by means of the tuning screw located one wavelength away from the diode in the opposite direction from the sliding short. This screw is used mainly to reduce "mode-hopping" and really should not be used to change frequency. The theory behind this method is that the introduction of a capacitance about a wavelength away from the diode results in a frequency that produces a low impedance at that particular point in the waveguide. This theory assumes that standing waves exist in the guide and are of the  $TM_{10}$  mode. All other modes are assumed to produce high impedances at this spot and will therefore be cancelled by this effect.

#### 3.3 SCHOTTKY DIODE MIXER

The mixer circuitry employed here consists of a  $90^{\circ}$  branch-line hybrid, two Schottky diodes and a low-pass summing network. Port 1 (Figure 3-9) is the signal input port (R.F.) and port 2 is the local oscillator (L.O.) input port.

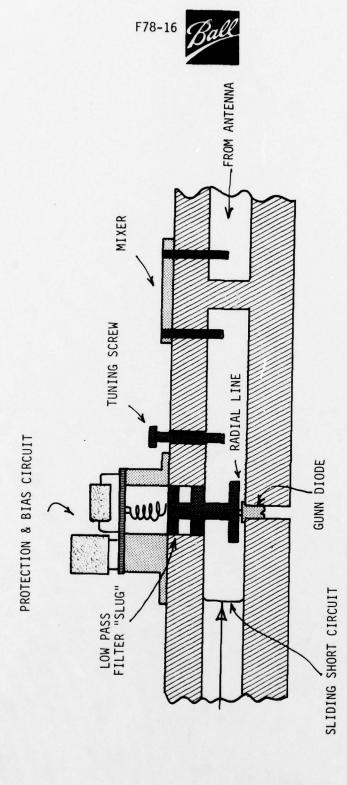


Figure 3-8 Oscillator Final Configuration



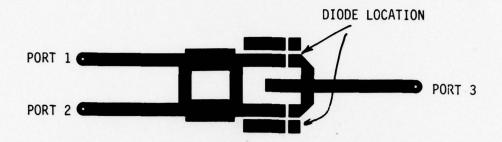


Figure 3-9 Layout for Schottky - Barrier Diode Mixer

This type of mixer configuration was chosen for its good VSWR, low conversion loss and good image rejection characteristics. Also because of its design, the image signal (2 L.O. - R.F.) will appear at the L.O. port. If this signal were to appear at the R.F. port, it is possible that reflection at some previous element (prior to mixer) would take place producing a second signal at the R.F. port and ultimately a signal or "image" at the I.F. frequency. A trade-off was made here and L.O./R.F. isolation was sacrificed to produce the best characteristics. This mixer type will commonly produce about 10 dB R.F. port to L.O. port isolation. Use of a 180° mixer would have produced only about 10 dB more isolation but would have sacrificed the other parameters, i.e. VSWR, conversion loss and image rejection.

The lack of high (>30 dB) R.F. port to L.O. port isolation will result in retransmission of a signal near the received signal (in frequency). This condition should not affect the incoming signal since it will be fairly well matched to the antenna and virtually no reflection will result.

Biasing of the mixer was considered for this development, but implementation of such techniques at Ka-band frequencies was thought to be too difficult for the return in better conversion loss. Also, biasing for low noise was not implemented for the same reasons.



The diodes are Alpha Industry Schottky barrier low noise beam-lead mixer diodes (DMK6606). Beam-lead diode packages were selected in order to reduce package parasitics and they lend themselves readily to MIC microstrip structures.

The summing and filtering port are of standard microstrip design. In this case, the summing function is merely an interconnect point for the mixed signal (difference) from either diode. Good, low VSWR design at this point is difficult as the diodes are operating in an extremely non-linear fashion and do not therefore have easily measurable reflection characteristics. However, an attempt to filter the local oscillator frequency component is made by introducing a open ended one-quarter wavelength stub at the summing position. This stub helps to reduce the L.O. signal at the I.F. port and provides a suitable return for R. F. energy from the local oscillator. A view of the bias circuit and mixer are shown in Figure 3-10.



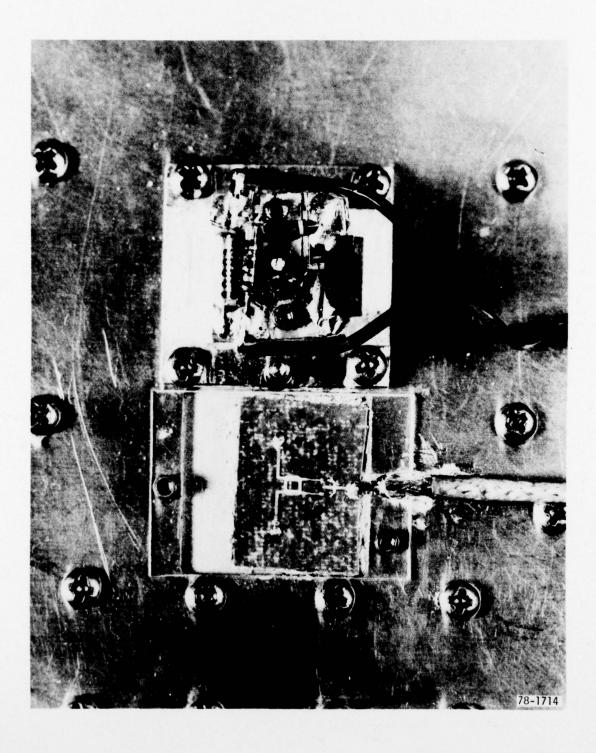


Figure 3-10 Protection-Bias Network and Mixer Photo



# Section 4

#### CONCLUSIONS AND RECOMMENDATIONS

#### 4.1 CONCLUSIONS

# • 32 x 32 Element Array

The loss budget shown in Table 2-2 indicates approximately 3.7 dB of unexplained loss which has been attributed to mismatches within the feed system. Along with the corresponding gain loss, these mismatches also disrupt the inter-element phase/amplitude relationships, resulting in degraded pattern performance.

Since the scaled model of the 32x32 element array tested at 13.8 GHz performed essentially as predicted, it would appear safe to assume that the problem is not caused by a faulty design. (Even with an all microstrip feed network, the array produced  $\approx 31$  dB of gain with nearly -20 dB sidelobes in both the E and H-planes).

#### Oscillator/Mixer

Although the mixer itself worked well, the oscillator produced considerable difficulty. Two problems were present from the beginning of operation of the oscillator and resulted in numerous diode failure and subsequently non-operative antenna-receiver systems. The first problem was that of bias circuit oscillation. It was found upon careful analysis of the bias circuit that an oscillation of the form found in relaxation-type oscillators could occur in the frequency range from 100 to 800 kHz. This problem was particularly difficult to spot as normal spectrum analysis did not provide enough resolution to show that oscillation was actually occurring. Secondly, these oscillations usually destroyed the diode in short order on an intermittent basis, so unless one was looking in the right place at the right time, everything appeared normal until sudden destruction occurred.



The second problem was that of multi-mode oscillations occurring in the wave guide itself. It was found that the oscillator would "jump" frequencies or oscillate at several frequencies at the same time depending on bias conditions and slider (sliding short circuit) position. In the final analysis the conclusion was that the oscillator was over-coupled to the mixer and was therefore very dependent on the impedance presented by the mixer. The mixer impedance, however, was very dependent on input level and therefore presented different impedances to the oscillator under different oscillator output levels. This interdependence along with the overcoupled condition made the oscillator more dependent upon the load presented to it than the cavity designed to determine the oscillator frequency. The results were then that the oscillator frequency was quite dependent upon its own output level. This problem did not occur during breadboard operation as some cable interconnection was required and the overcoupled condition did not exist.

The mixer performed well giving trouble only in fabrication stages and initial design stages. Conversion loss was a problem initially due to diode-coupler matching but was improved in subsequent design. The output impedance was not  $50\Omega$  as expected but was much lower and of the order of  $10\text{--}15\Omega$ . This results in an apparent conversion loss of near 16 dB but it is expected that with external matching the conversion loss can be improved to near 12 dB.

# 4.2 RECOMMENDATIONS

#### • 32 x 32 Element Array

Although some improvement in performance could probably be obtained by further refinements of the array feed system (waveguide and microstrip), it is felt that a detailed investigation of candidate substrate materials would result in the largest improvement in performance.



It may be necessary to employ substrates such as quartz to achieve the dielectric uniformity and low-loss tangent required for large arrays at millimeter frequencies.

### Oscillator/Mixer

The recommendation for the oscillator circuit would be a complete redesign based on a TEM structure. In this case, a coaxial type oscillator is proposed, using a positioned iris for coupling to waveguide or a simple resistive pad for isolation from the mixer. This circuit would have no tendency to oscillate at frequencies other than those described by the coaxial resonant circuit and would be more easily coupled to the mixer as both would be TEM mode circuits. This circuit also allows use of simpler biasing techniques and subsequent reduction in bias circuit induced oscillations.

The mixer performed well, although conversion loss was still not as good as hoped for. The solution here is merely better output matching and some slight changes in transmission line transformers for hybrid coupler to diode matching. Some work could also be done for noise figure improvement by possibly adding bias circuitry to the mixer.